

SKM100GAL12T4



SEMITRANS® 2

Fast IGBT4 Modules

SKM100GAL12T4

Features

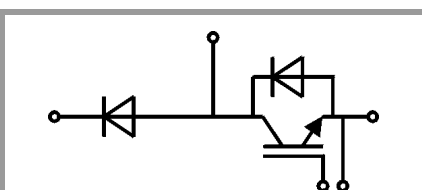
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability, self limiting to 6 x I_{Cnom}
- Fast & soft inverse CAL diodes
- Large clearance (10 mm) and creepage distances (20 mm)
- Isolated copper baseplate using DBC Technology (Direct Copper Bonding)
- UL recognized, file no. E63532

Typical Applications*

- DC/DC – converter
- Brake chopper
- Switched reluctance motor
- DC – motor

Remarks

- Case temperature limited to $T_c = 125^\circ\text{C}$ max, recomm.
 $T_{op} = -40 \dots +150^\circ\text{C}$, product rel. results valid for $T_j = 150^\circ$



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Absolute Maximum Ratings

Symbol	Conditions	Values	Unit
IGBT			
V_{CES}	$T_j = 25^\circ\text{C}$	1200	V
I_C	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	160
		$T_c = 80^\circ\text{C}$	123
I_{Cnom}		100	A
I_{CRM}	$I_{CRM} = 3 \times I_{Cnom}$	300	A
V_{GES}		-20 ... 20	V
t_{psc}	$V_{CC} = 800\text{ V}$ $V_{GE} \leq 15\text{ V}$ $V_{CES} \leq 1200\text{ V}$	$T_j = 150^\circ\text{C}$	10
T_j		-40 ... 175	$^\circ\text{C}$

Inverse diode

I_F	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	121	A
		$T_c = 80^\circ\text{C}$	91	A
I_{Fnom}			100	A
I_{FRM}	$I_{FRM} = 3 \times I_{Fnom}$		300	A
I_{FSM}	$t_p = 10\text{ ms, sin } 180^\circ, T_j = 25^\circ\text{C}$		550	A
T_j			-40 ... 175	$^\circ\text{C}$

Freewheeling diode

I_F	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	121	A
		$T_c = 80^\circ\text{C}$	91	A
I_{Fnom}			100	A
I_{FRM}	$I_{FRM} = 3 \times I_{Fnom}$		300	A
I_{FSM}	$t_p = 10\text{ ms, sin } 180^\circ, T_j = 25^\circ\text{C}$		550	A
T_j			-40 ... 175	$^\circ\text{C}$

Module

$I_{t(RMS)}$	$T_{terminal} = T_{terminal} < 80^\circ\text{C}$	200	A
T_{stg}		-40 ... 125	$^\circ\text{C}$
V_{isol}	AC sinus 50Hz, $t = 1\text{ min}$	4000	V

Characteristics

Symbol	Conditions	min.	typ.	max.	Unit
IGBT					
$V_{CE(sat)}$	$I_C = 100\text{ A}$ $V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	1.8	2.05	V
		$T_j = 150^\circ\text{C}$	2.2	2.4	V
V_{CE0}		$T_j = 25^\circ\text{C}$	0.8	0.9	V
		$T_j = 150^\circ\text{C}$	0.7	0.8	V
r_{CE}	$V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}$	10.0	11.5	m Ω
		$T_j = 150^\circ\text{C}$	15.0	16.0	m Ω
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 3.8\text{ mA}$	5	5.8	6.5	V
I_{CES}	$V_{GE} = 0\text{ V}$ $V_{CE} = 1200\text{ V}$	$T_j = 25^\circ\text{C}$	0.1	0.3	mA
		$T_j = 150^\circ\text{C}$			mA
C_{ies}	$V_{CE} = 25\text{ V}$		6.15		nF
C_{oes}	$V_{GE} = 0\text{ V}$		0.40		nF
C_{res}			0.345		nF
Q_G	$V_{GE} = -8\text{ V} \dots +15\text{ V}$		565		nC
R_{Gint}	$T_j = 25^\circ\text{C}$		7.5		Ω

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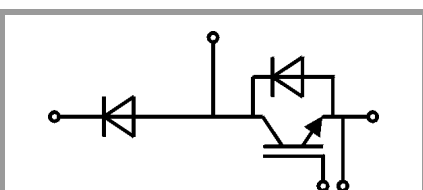
Typical Applications*

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Remarks

- Case temperature limited to $T_c = 125^\circ\text{C}$ max, recomm.
 $T_{op} = -40 \dots +150^\circ\text{C}$, product rel. results valid for $T_j = 150^\circ$

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
$t_{d(on)}$	$V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$		165		ns
t_r	$I_C = 100\text{ A}$	$T_j = 150^\circ\text{C}$		47		ns
E_{on}	$V_{GE} = \pm 15\text{ V}$	$T_j = 150^\circ\text{C}$		15		mJ
$t_{d(off)}$	$R_{G\ on} = 1\ \Omega$	$T_j = 150^\circ\text{C}$		400		ns
t_f	$R_{G\ off} = 1\ \Omega$	$T_j = 150^\circ\text{C}$		75		ns
E_{off}	$di/dt_{on} = 1800\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$		10.2		mJ
	$di/dt_{off} = 1130\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$				
$R_{th(j-c)}$	per IGBT				0.27	K/W
Inverse diode						
$V_F = V_{EC}$	$I_F = 100\text{ A}$	$T_j = 25^\circ\text{C}$		2.20	2.52	V
	$V_{GE} = 0\text{ V}$	$T_j = 150^\circ\text{C}$		2.15	2.47	V
	chip					
V_{F0}		$T_j = 25^\circ\text{C}$		1.3	1.5	V
		$T_j = 150^\circ\text{C}$		0.9	1.1	V
r_F		$T_j = 25^\circ\text{C}$		9.0	10.2	m Ω
		$T_j = 150^\circ\text{C}$		12.5	13.7	m Ω
I_{RRM}	$I_F = 100\text{ A}$	$T_j = 150^\circ\text{C}$		54		A
Q_{rr}	$di/dt_{off} = 1600\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$		15.7		μC
E_{rr}	$V_{GE} = \pm 15\text{ V}$	$T_j = 150^\circ\text{C}$		5.9		mJ
	$V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$				
$R_{th(j-c)}$	per diode				0.48	K/W
Freewheeling diode						
$V_F = V_{EC}$	$I_F = 100\text{ A}$	$T_j = 25^\circ\text{C}$		2.20	2.52	V
	$V_{GE} = 0\text{ V}$	$T_j = 150^\circ\text{C}$		2.15	2.47	V
	chip					
V_{F0}		$T_j = 25^\circ\text{C}$		1.3	1.5	V
		$T_j = 150^\circ\text{C}$		0.9	1.1	V
r_F		$T_j = 25^\circ\text{C}$		9.0	10.2	m Ω
		$T_j = 150^\circ\text{C}$		12.5	13.7	m Ω
I_{RRM}	$I_F = 100\text{ A}$	$T_j = 150^\circ\text{C}$		165		A
Q_{rr}	$di/dt_{off} = 1600\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$		15.7		μC
E_{rr}	$V_{GE} = \pm 15\text{ V}$	$T_j = 150^\circ\text{C}$		5.9		mJ
	$V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$				
$R_{th(j-c)}$	per Diode				0.48	K/W
Module						
L_{CE}					30	nH
$R_{CC'+EE'}$	terminal-chip	$T_c = 25^\circ\text{C}$		0.65		m Ω
		$T_c = 125^\circ\text{C}$		1		m Ω
$R_{th(c-s)}$	per module			0.04	0.05	K/W
M_s	to heat sink M6		3		5	Nm
M_t		to terminals M5	2.5		5	Nm
						Nm
w					160	g



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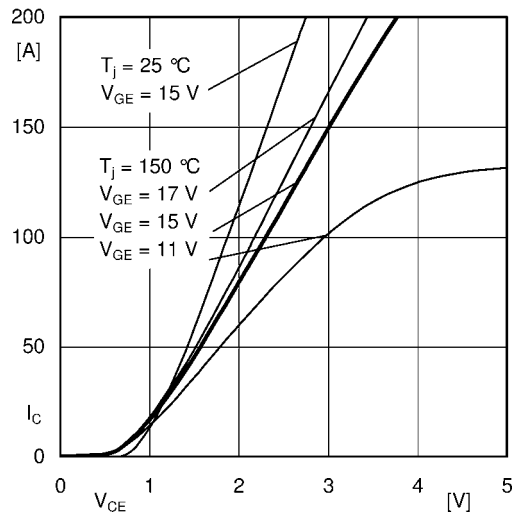


Fig. 1: Typ. output characteristic, inclusive $R_{CC'+EE'}$

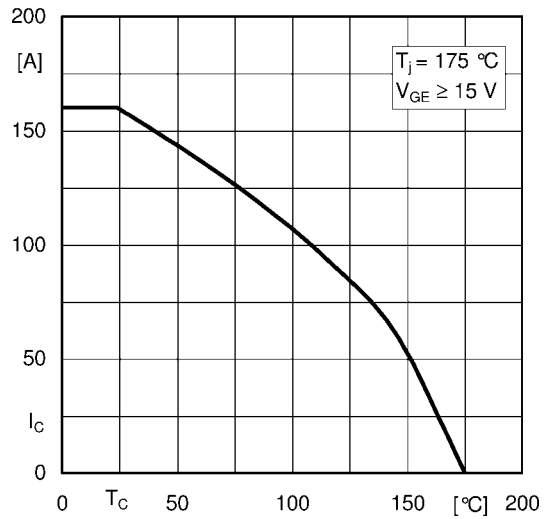


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

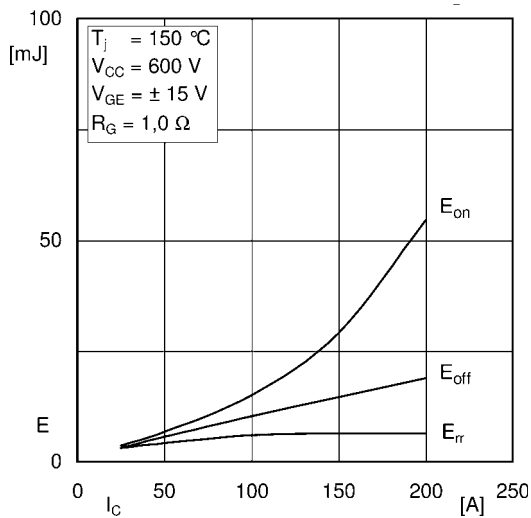


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

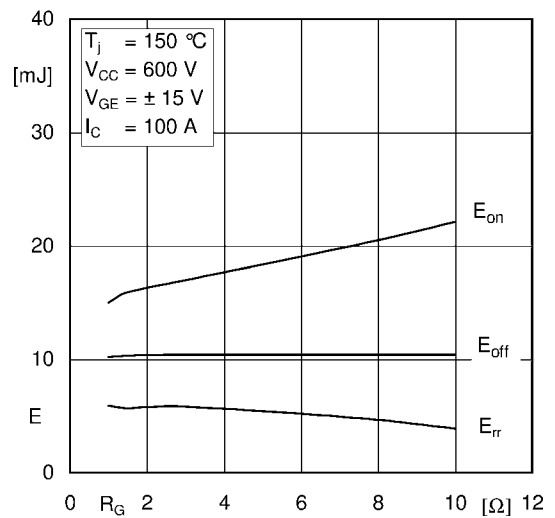


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

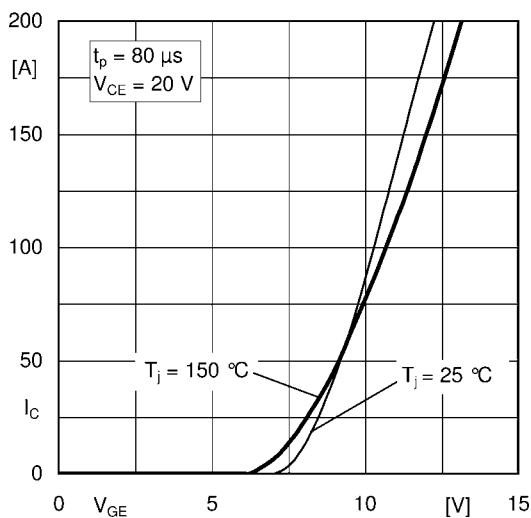


Fig. 5: Typ. transfer characteristic

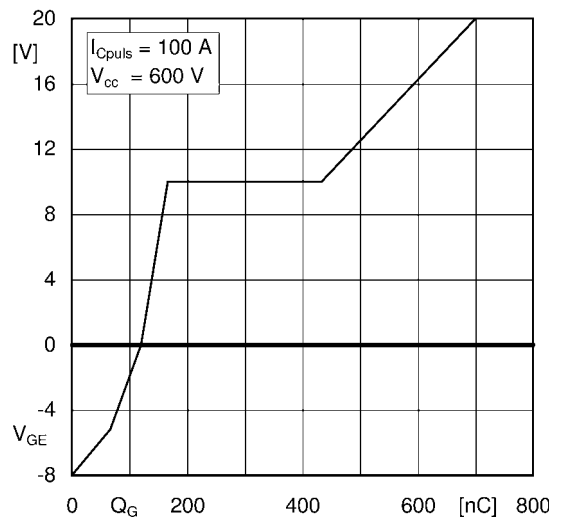


Fig. 6: Typ. gate charge characteristic

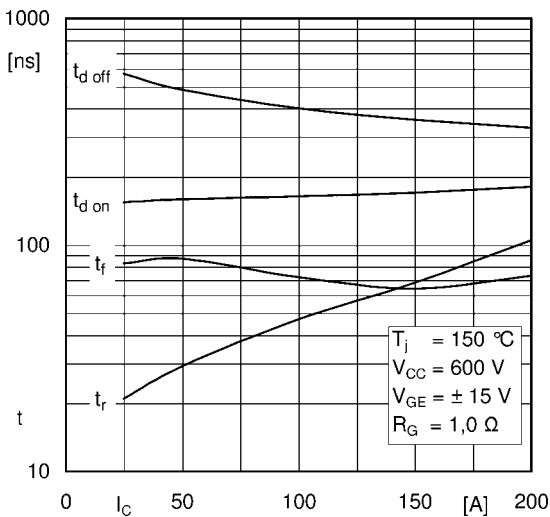


Fig. 7: Typ. switching times vs. I_C

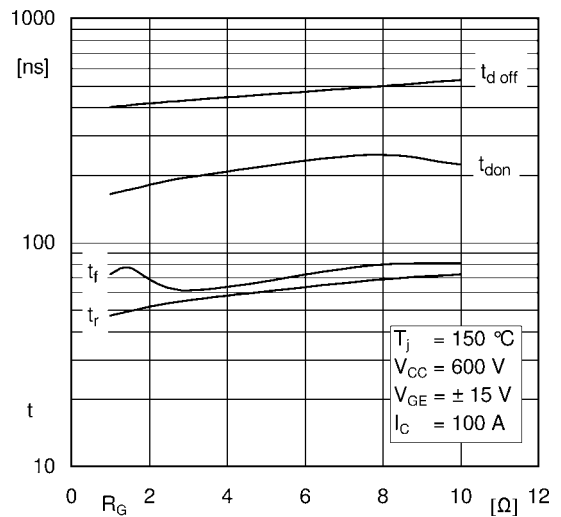


Fig. 8: Typ. switching times vs. gate resistor R_G

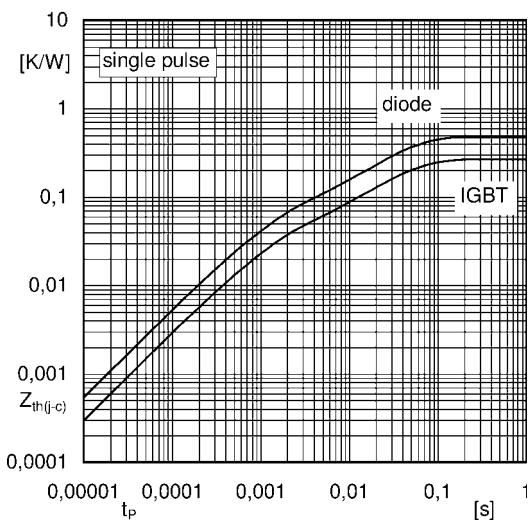


Fig. 9: Transient thermal impedance

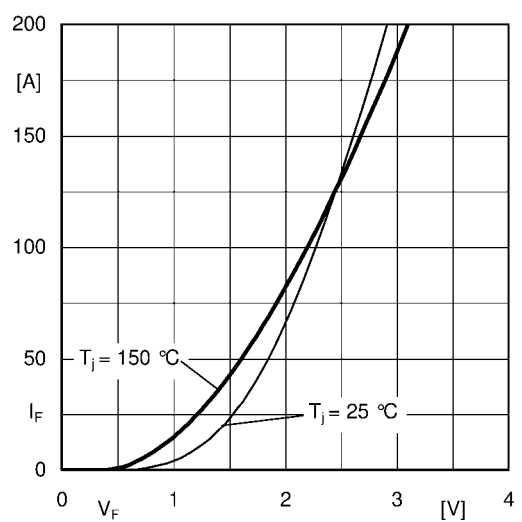


Fig. 10: Typ. CAL diode forward charact., incl. $R_{CC+EE'}$

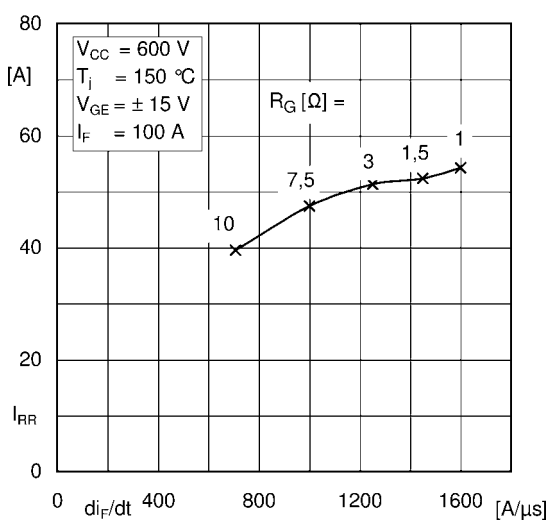


Fig. 11: CAL diode peak reverse recovery current

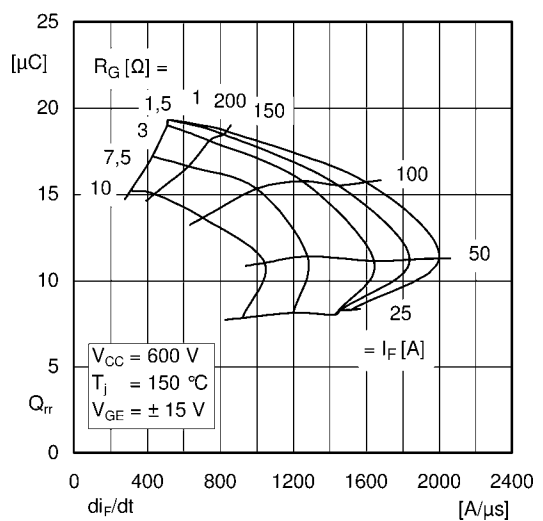
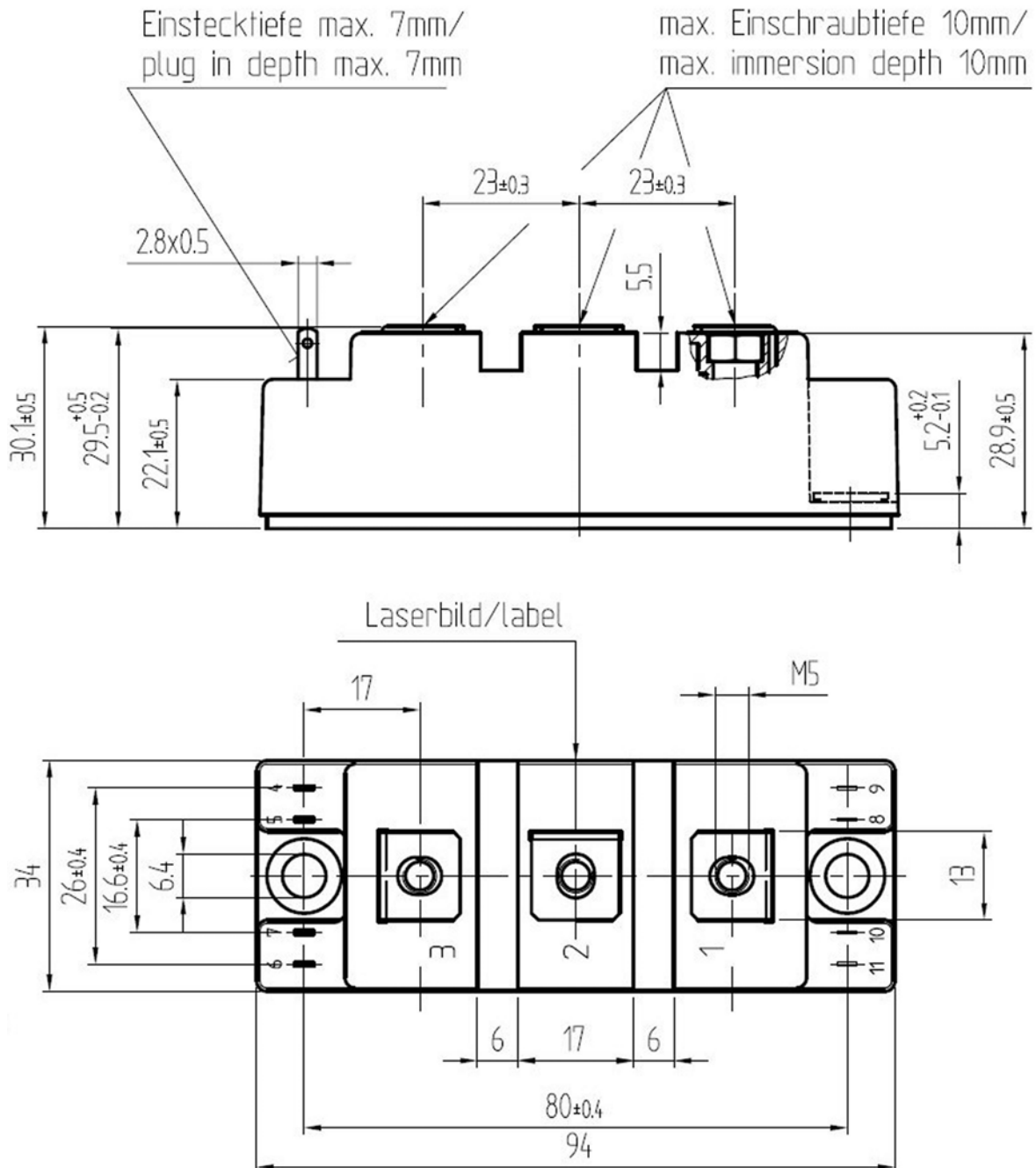
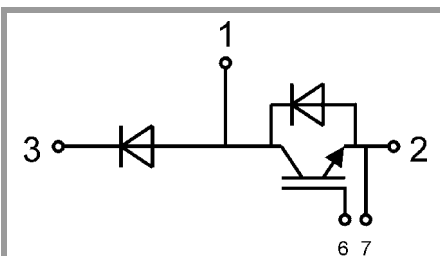


Fig. 12: Typ. CAL diode peak reverse recovery charge

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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.